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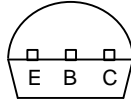
2SC2216

Features

- Capable of 300mWatts of Power Dissipation.
- Collector-current 50mA
- Collector-base Voltage 50V
- Operating and storage junction temperature range: -55°C to +150°C

NPN Silicon Plastic-Encapsulate Transistor

Pin Configuration
Bottom View



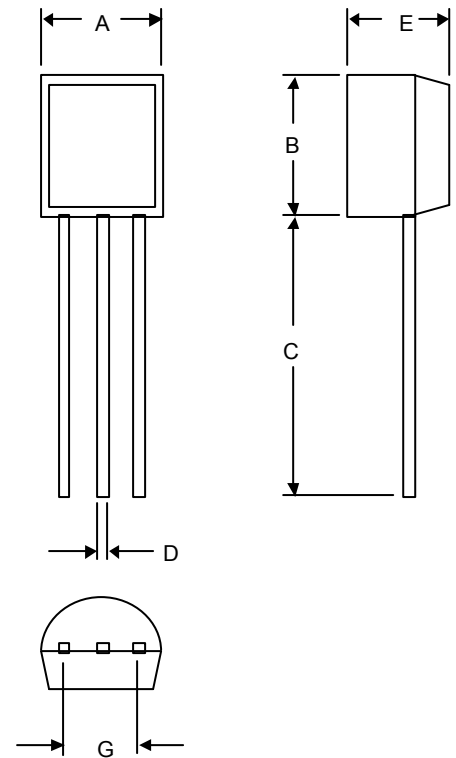
Electrical Characteristics @ 25°C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage ($I_C=10mA$, $I_B=0$)	45	---	Vdc
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage ($I_C=100\mu A$, $I_E=0$)	50	---	Vdc
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_E=100\mu A$, $I_C=0$)	4.0	---	Adc
I_{CBO}	Collector Cutoff Current ($V_{CB}=50Vdc$, $I_E=0$)	---	0.1	μA
I_{EBO}	Emitter Cutoff Current ($V_{EB}=4.0Vdc$, $I_C=0$)	---	0.1	μA

ON CHARACTERISTICS

h_{FE}	DC Current Gain ($I_C=12.5mA$, $V_{CE}=12.5Vdc$)	40	140	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage ($I_C=15mA$, $I_B=1.5mA$)	---	0.2	Vdc
$V_{(BE)sat}$	Base-Emitter Saturation Voltage ($I_C=15mA$, $I_B=1.5mA$)	---	1.5	Vdc
fT	Transition Frequency ($V_{CE}=12.5Vdc$, $I_C=12.5mA$, f=100MHz)	300	---	MHz

TO-92



DIMENSIONS

DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.170	.190	4.33	4.83	
B	.170	.190	4.30	4.83	
C	.550	.590	13.97	14.97	
D	.010	.020	0.36	0.56	
E	.130	.160	3.30	3.96	
G	.010	.104	2.44	2.64	